

## Silicon PNP Power Transistors

## 2SB550

**DESCRIPTION**

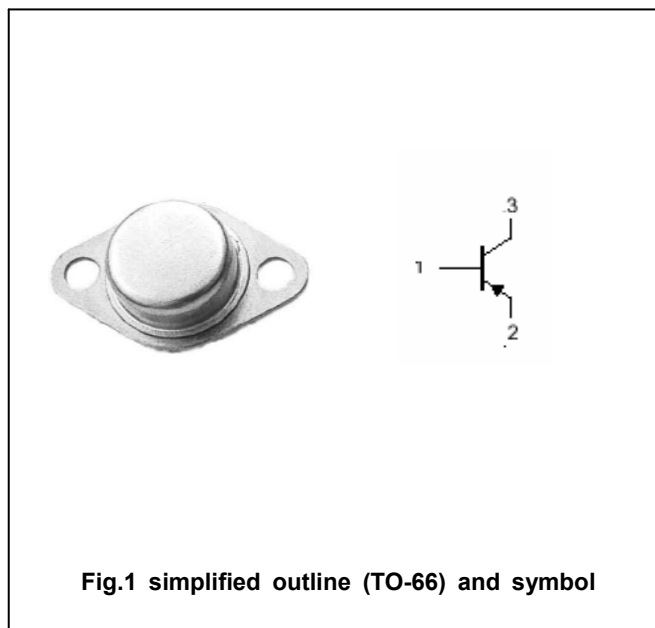
- With TO-66 package
- Low collector saturation voltage

**APPLICATIONS**

- For low frequency power amplification
- For low speed and power switching

**PINNING(see Fig.2)**

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

**Absolute maximum ratings(Ta=□)**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CBO</sub>	Collector-base voltage	Open emitter	-100	V
V <sub>CEO</sub>	Collector-emitter voltage	Open base	-70	V
V <sub>EBO</sub>	Emitter-base voltage	Open collector	-5	V
I <sub>C</sub>	Collector current		-5	A
P <sub>C</sub>	Collector power dissipation	T <sub>C</sub> =25□	25	W
T <sub>j</sub>	Junction temperature		150	□
T <sub>stg</sub>	Storage temperature		-55~150	□

## Silicon PNP Power Transistors

## 2SB550

## CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CBO}$	Collector-base breakdown voltage	$I_C = -1\text{mA}; I_E = 0$	-100			V
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C = -10\text{mA}; I_B = 0$	-70			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E = -1\text{mA}; I_C = 0$	-5			V
$V_{CEsat}$	Collector-emitter saturation voltage	$I_C = -5\text{A}; I_B = -0.5\text{A}$			-1.0	V
$V_{BEsat}$	Base-emitter saturation voltage	$I_C = -5\text{A}; I_B = -0.5\text{A}$			-1.5	V
$I_{CBO}$	Collector cut-off current	$V_{CB} = -80\text{V}; I_E = 0$			-0.1	mA
$I_{EBO}$	Emitter cut-off current	$V_{EB} = -5\text{V}; I_C = 0$			-0.1	mA
$h_{FE}$	DC current gain	$I_C = -1\text{A}; V_{CE} = -5\text{V}$	30		200	
$f_T$	Transition frequency	$I_C = -0.1\text{A}; V_{CE} = -10\text{V}$		5		MHz

Silicon PNP Power Transistors

2SB550

PACKAGE OUTLINE



Fig.2 outline dimensions